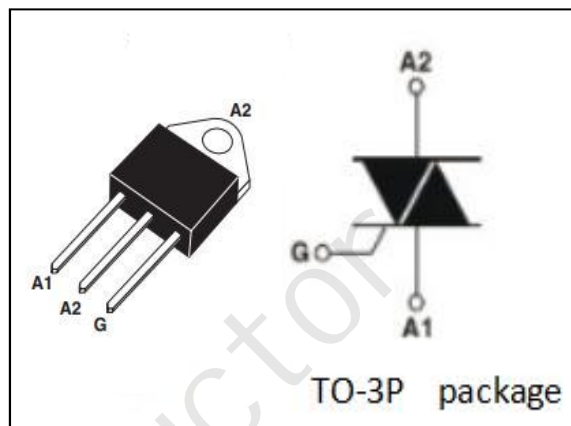


**DESCRIPTION**

- With TO-3P packaging
- Operating in 4 quadrants
- High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

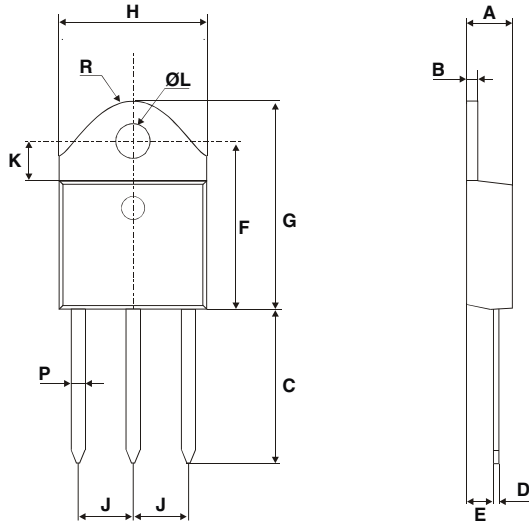
- Switching applications
- Phase control
- Static switching on inductive or resistive load


**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	MAX	UNIT
V <sub>DRM</sub>	Repetitive peak off-state voltage	800	V
V <sub>RRM</sub>	Repetitive peak reverse voltage	800	V
I <sub>T(RSM)</sub>	Average on-state current T <sub>c</sub> =105°C	25	A
I <sub>TSM</sub>	Surge non-repetitive on-state current	250 260	A
P <sub>G(AV)</sub>	Average gate power dissipation ( over any 20 ms period ) T <sub>j</sub> =125°C	1	W
T <sub>j</sub>	Operating junction temperature	-40~125	°C
T <sub>stg</sub>	Storage temperature	-40~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise specified)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I <sub>RRM</sub>	Repetitive peak reverse current	V <sub>R</sub> =V <sub>RRM</sub> Rated; T <sub>j</sub> =25°C		5	μA
I <sub>DRM</sub>	Repetitive peak off-state current	V <sub>D</sub> =V <sub>DRM</sub> Rated; T <sub>j</sub> =125°C		3	mA
V <sub>TM</sub>	On-state voltage	I <sub>T</sub> =35A; t <sub>p</sub> =380 μs		1.55	V
I <sub>GT</sub>	Gate-trigger current	V <sub>D</sub> = 12V; R <sub>L</sub> =33Ω;	I	35	mA
			II	35	
			III	35	
			IV	50	
V <sub>GT</sub>	Gate-trigger voltage	V <sub>D</sub> = 12V; R <sub>L</sub> =33Ω;		1.3	V
R <sub>th(j-c)</sub>	Junction to case			0.6	°C/W

**TO-3P (Insulated and non insulated) Package Mechanical Data**


REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.5		0.7	0.020		0.028
E	2.7		2.9	0.106		0.114
F	15.8		16.5	0.622		0.650
G	20.4		21.1	0.815		0.831
H	15.1		15.5	0.594		0.610
J	5.4		5.65	0.213		0.222
K	3.4		3.65	0.134		0.144
ØL	4.08		4.17	0.161		0.164
P	1.20		1.40	0.047		0.055
R		4.60			0.181	